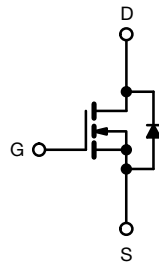
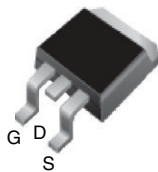


Power MOSFET

D²PAK (TO-263)

N-Channel MOSFET

PRODUCT SUMMARY

V_{DS} (V)	100
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$ 0.54
Q_g max. (nC)	8.3
Q_{gs} (nC)	2.3
Q_{gd} (nC)	3.8
Configuration	Single

FEATURES

- Surface-mount
- Available in tape and reel
- Dynamic dv/dt rating
- Repetitive avalanche rated
- 175 °C operating temperature
- Fast switching
- Ease of paralleling
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details



RoHS*
Available
HALOGEN
FREE
Available

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D²PAK (TO-263) is a surface-mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface-mount package. The D²PAK (TO-263) is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface-mount application.

ORDERING INFORMATION

Package	D ² PAK (TO-263)	D ² PAK (TO-263)	D ² PAK (TO-263)
Lead (Pb)-free and halogen-free	SiHF510S-GE3	SiHF510STRL-GE3 ^a	SiHF510STRR-GE3 ^a
Lead (Pb)-free	IRF510SPbF	IRF510STRLPbF ^a	IRF510STRRPbF ^a

Note

a. See device orientation

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	100	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	I_D	5.6	A
		4.0	
Pulsed drain current ^a	I_{DM}	20	
Linear derating factor		0.29	W/°C
Linear derating factor (PCB mount) ^e		0.025	
Single pulse avalanche energy ^b	E_{AS}	75	mJ
Avalanche current ^a	I_{AR}	5.6	A
Repetitive avalanche energy ^a	E_{AR}	4.3	mJ
Maximum power dissipation	P_D	43	W
Maximum power dissipation (PCB mount) ^e		3.7	
Peak diode recovery dv/dt ^c	dv/dt	5.5	V/ns
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^d	For 10 s	300	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = 25\text{ V}$, starting $T_J = 25\text{ °C}$, $L = 4.8\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 5.6\text{ A}$ (see fig. 12)
- $I_{SD} \leq 5.6\text{ A}$, $di/dt \leq 75\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 175\text{ °C}$
- 1.6 mm from case
- When mounted on 1" square PCB (FR-4 or G-10 material)

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Maximum junction-to-ambient (PCB mount) ^a	R_{thJA}	-	40	
Maximum junction-to-case (drain)	R_{thJC}	-	3.5	

Note

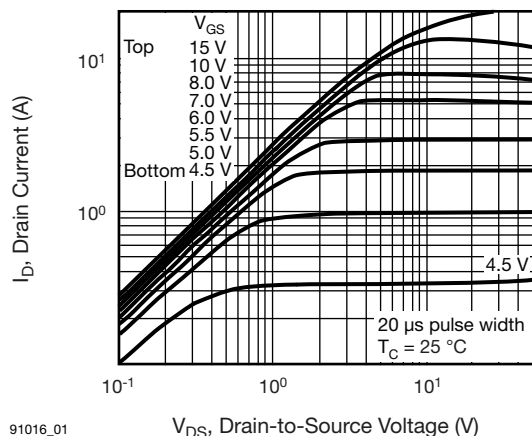
a. When mounted on 1" square PCB (FR-4 or G-10 material)

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

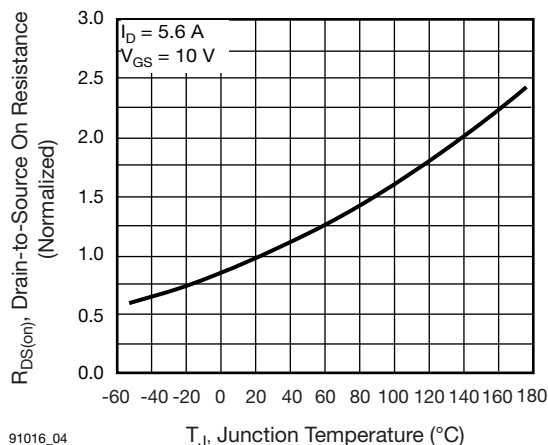
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0$, $I_D = 250\text{ }\mu\text{A}$		100	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.12	-	V/ $^\circ\text{C}$
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 100\text{ V}$, $V_{GS} = 0\text{ V}$		-	-	25	μA
		$V_{DS} = 80\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$		-	-	250	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 3.4\text{ A}^b$	-	-	0.54	Ω
Forward transconductance	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 3.4\text{ A}^b$		1.3	-	-	S
Dynamic							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5		-	180	-	pF
Output capacitance	C_{oss}			-	81	-	
Reverse transfer capacitance	C_{rss}			-	15	-	
Total gate charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 5.6\text{ A}$, $V_{DS} = 80\text{ V}$, see fig. 6 and fig. 13 ^b	-	-	8.3	nC
Gate-source charge	Q_{gs}			-	-	2.3	
Gate-drain charge	Q_{gd}			-	-	3.8	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50\text{ V}$, $I_D = 5.6\text{ A}$, $R_g = 24\text{ }\Omega$, $R_D = 8.4\text{ }\Omega$, see fig. 10 ^b		-	6.9	-	ns
Rise time	t_r			-	16	-	
Turn-off delay time	$t_{d(off)}$			-	15	-	
Fall time	t_f			-	9.4	-	
Gate input resistance	R_g	$f = 1\text{ MHz}$, open drain		2.5	-	11.6	Ω
Internal drain inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal source inductance	L_S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	5.6	A
Pulsed diode forward current ^a	I_{SM}			-	-	20	
Body diode voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}$, $I_S = 5.6\text{ A}$, $V_{GS} = 0\text{ V}^b$		-	-	2.5	V
Body diode reverse recovery time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$, $I_F = 5.6\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}^b$		-	100	200	ns
Body diode reverse recovery charge	Q_{rr}			-	0.44	0.88	μC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

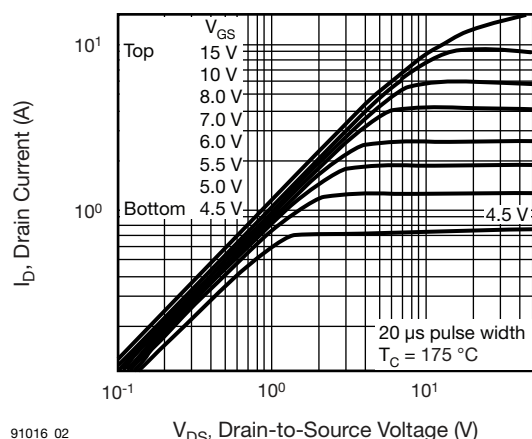
- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


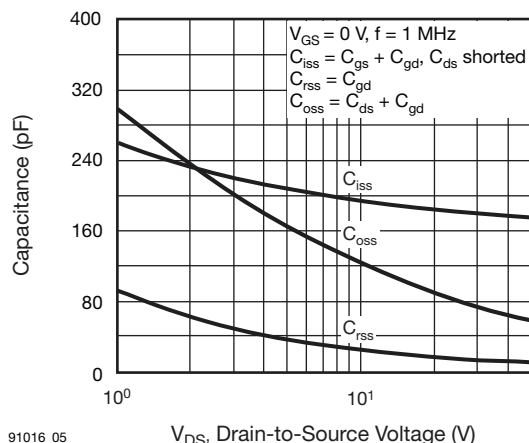
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Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^{\circ}\text{C}$


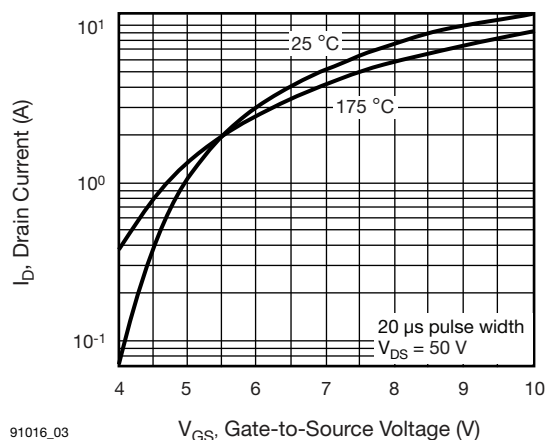
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Fig. 4 - Normalized On-Resistance vs. Temperature


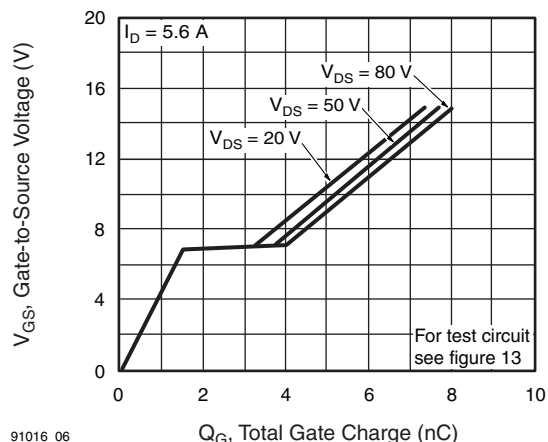
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Fig. 2 - Typical Output Characteristics, $T_C = 175\text{ }^{\circ}\text{C}$


91016_05

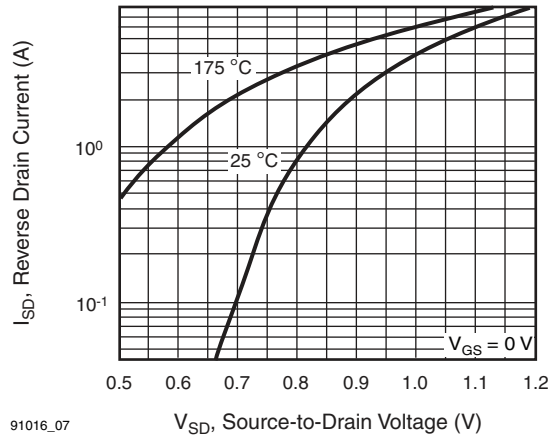
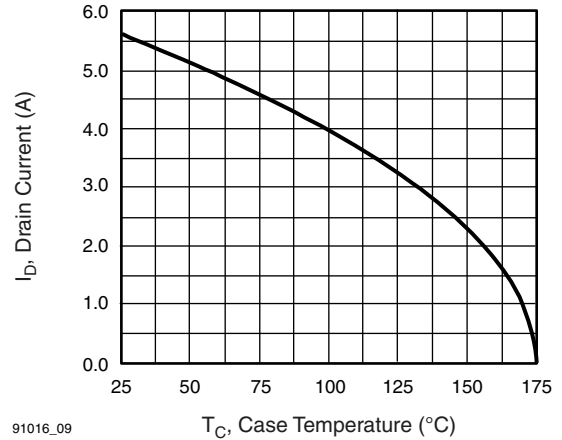
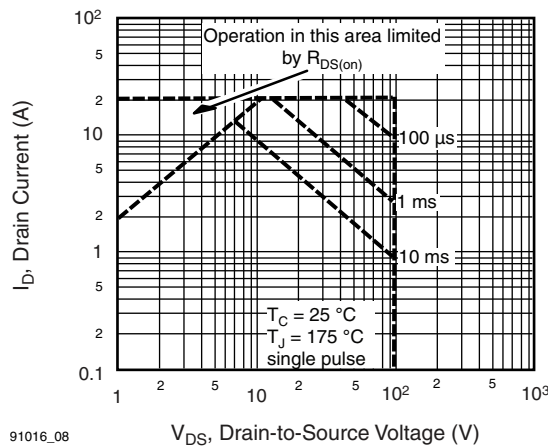
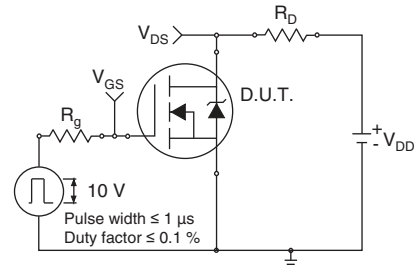
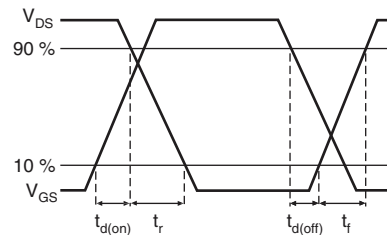
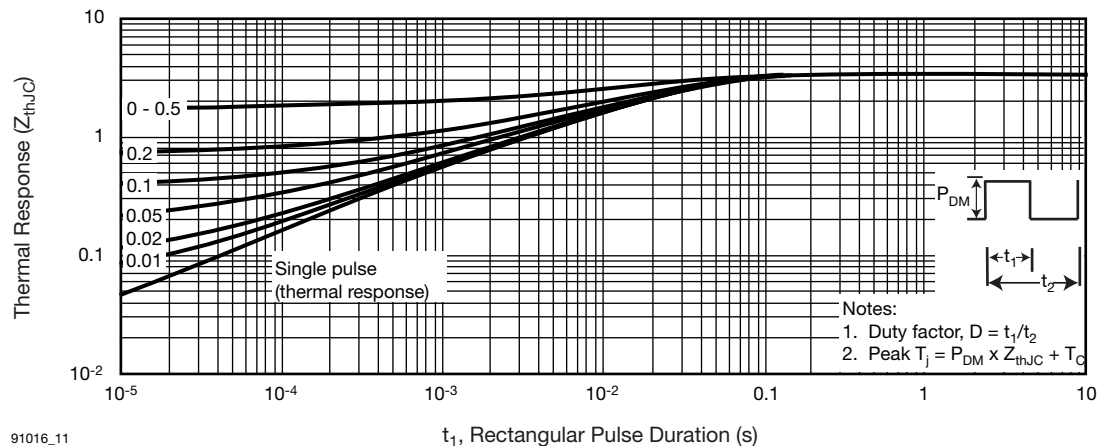
Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage


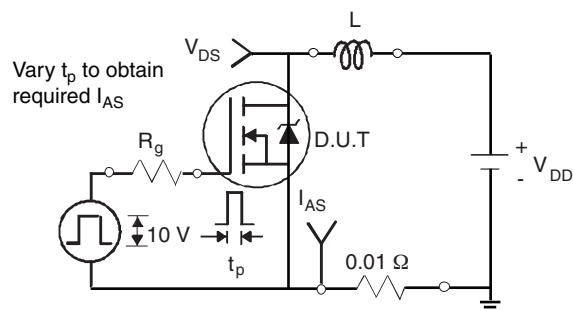
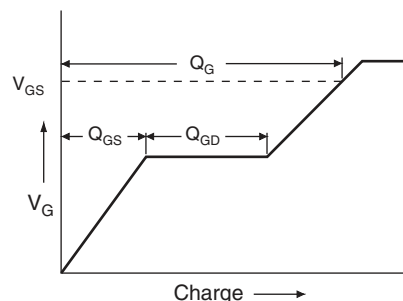
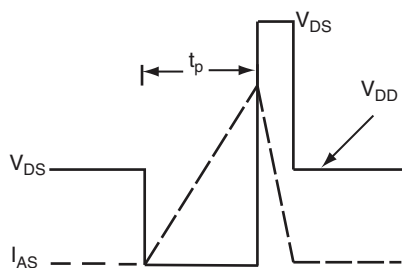
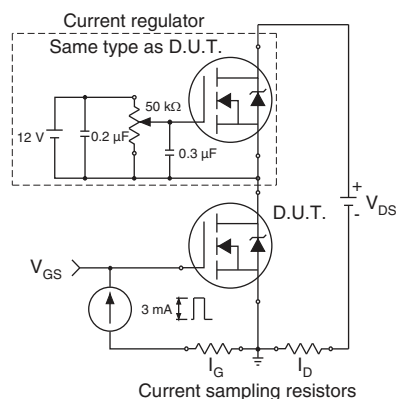
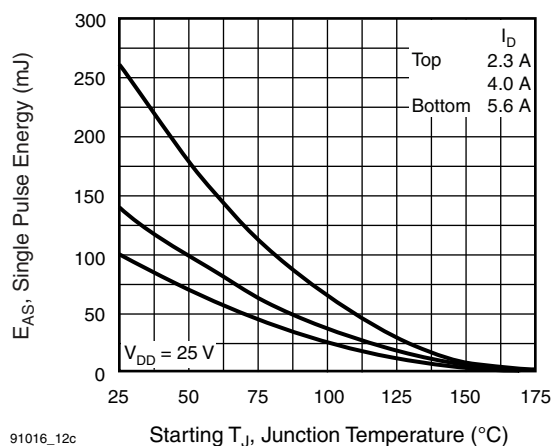
91016_03

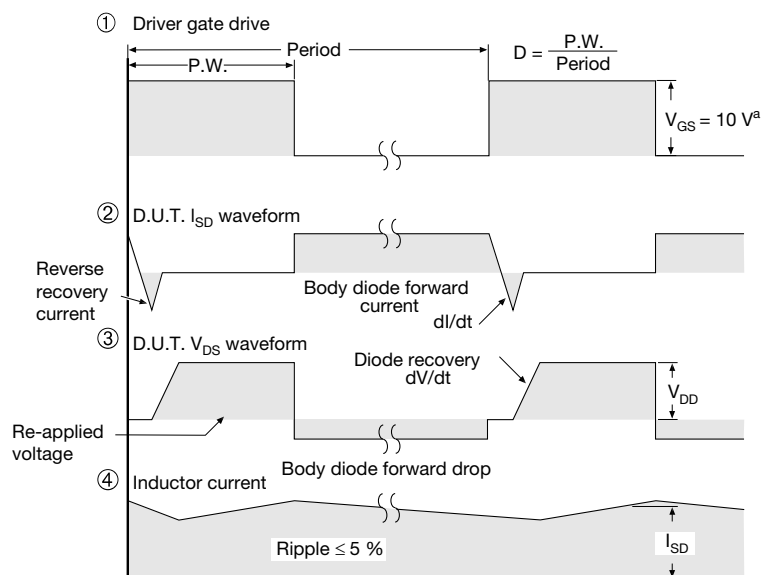
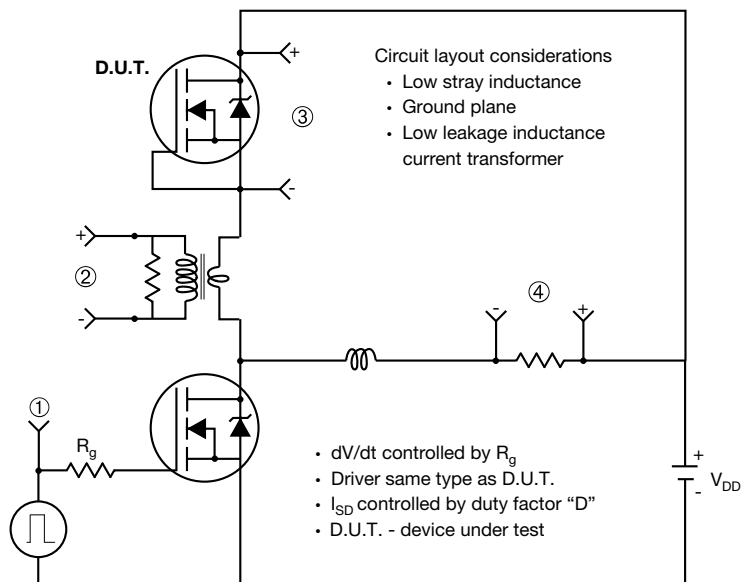
Fig. 3 - Typical Transfer Characteristics


91016_06

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage


Fig. 7 - Typical Source-Drain Diode Forward Voltage

Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Maximum Safe Operating Area

Fig. 10a - Switching Time Test Circuit

Fig. 10b - Switching Time Waveforms

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case


Fig. 12a - Unclamped Inductive Test Circuit

Fig. 13a - Basic Gate Charge Waveform

Fig. 12b - Unclamped Inductive Waveforms

Fig. 13b - Gate Charge Test Circuit

Fig. 12c - Maximum Avalanche Energy vs. Drain Current

Peak Diode Recovery dV/dt Test Circuit

Note

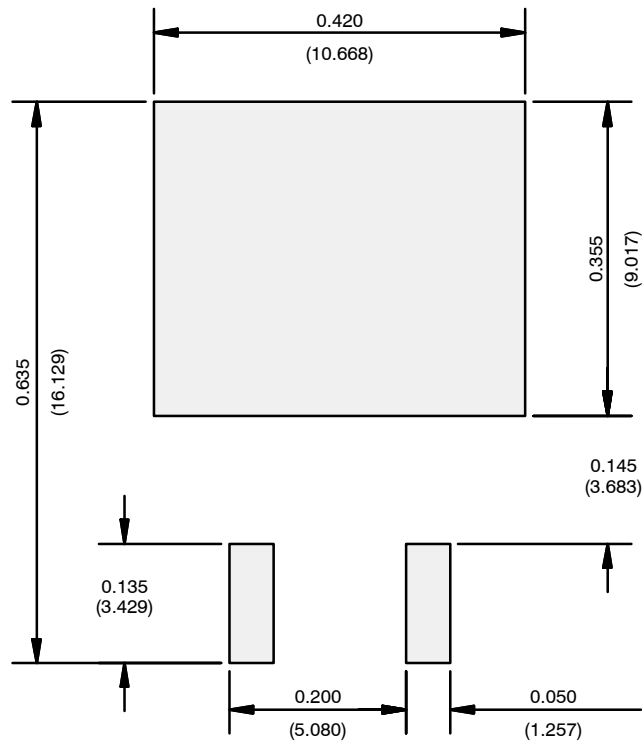
a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 14 - For N-Channel

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	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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